

N-Channel Logic Level Enhancement Mode Power MOSFET

MTB11N03Q8

| | |
|--------------------------|-------|
| BV _{DSS} | 30V |
| I _D | 16A |
| R _{DS(on)(max)} | 8.5mΩ |

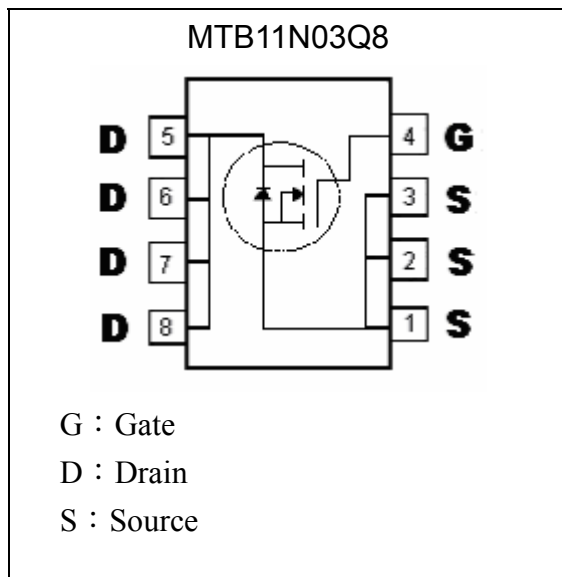
Description

The MTB11N03Q8 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The SOP-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

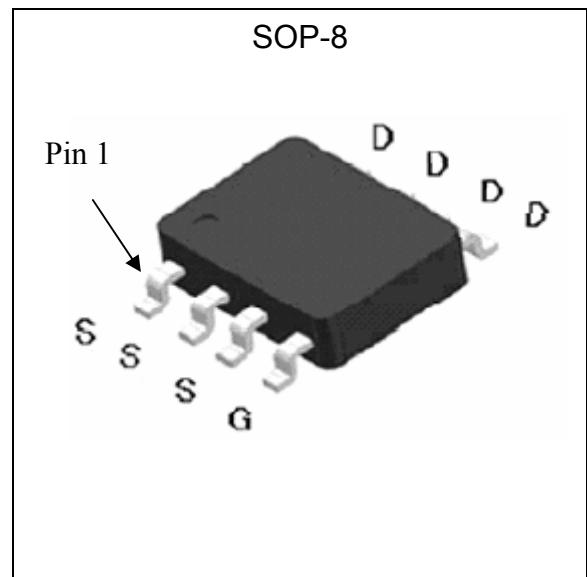
Features

- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Dynamic dv/dt rating
- Repetitive Avalanche Rated
- Pb-free and Halogen-free package

Symbol



Outline





Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Limits | Unit |
|--|-----------------------------------|---------------------------------|------|
| Drain-Source Voltage | V _{DS} | 30 | V |
| Gate-Source Voltage | V _{GS} | ±20 | |
| Continuous Drain Current @ T _A =25°C, V _{GS} =10V | I _D | 16 *3 | A |
| Continuous Drain Current @ T _A =100°C, V _{GS} =10V | | 10 *3 | |
| Pulsed Drain Current | | 50 *1 | |
| Avalanche Current | I _{AS} | 16 | mJ |
| Avalanche Energy @ L=0.1mH, I _D =11A, R _G =25Ω | E _{AS} | 9.8 | |
| Repetitive Avalanche Energy @ L=0.05mH | E _{AR} | 4.9 *2 | |
| Total Power Dissipation | P _D | T _A =25°C 3.1 *3 | W |
| | | T _A =100°C 1.2 *3 | |
| Operating Junction and Storage Temperature Range | T _j , T _{stg} | -55~+150 | °C |

Thermal Data

| Parameter | Symbol | Value | Unit |
|--|---------------------|-------|------|
| Thermal Resistance, Junction-to-case, max | R _{th,j-c} | 25 | °C/W |
| Thermal Resistance, Junction-to-ambient, max | R _{th,j-a} | 40 *3 | °C/W |

- Note : 1. Pulse width limited by maximum junction temperature.
 2. Duty cycle ≤ 1%.
 3. Surface mounted on 1 in² copper pad of FR-4 board, t ≤ 10s; 125°C/W when mounted on minimum copper pad.

Characteristics (Tc=25°C, unless otherwise specified)

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|------------------------|------|------|------|------|---|
| Static | | | | | |
| BV _{DSS} | 30 | - | - | V | V _{GS} =0, I _D =250μA |
| V _{GS(th)} | 1.0 | 1.5 | 3.0 | V | V _{DS} = V _{GS} , I _D =250μA |
| G _{FS} *1 | - | 20 | - | S | V _{DS} =5V, I _D =11A |
| I _{GSS} | - | - | ±100 | nA | V _{GS} =±20 |
| I _{DSS} | - | - | 1 | μA | V _{DS} =24V, V _{GS} =0 |
| | - | - | 25 | | V _{DS} =20V, V _{GS} =0, T _j =125°C |
| R _{DS(ON)} *1 | - | 6.7 | 8.5 | mΩ | V _{GS} =10V, I _D =16A |
| | - | 10 | 13.5 | mΩ | V _{GS} =4.5V, I _D =12A |
| Dynamic | | | | | |
| C _{iss} | - | 1638 | - | pF | V _{GS} =0V, V _{DS} =15V, f=1MHz |
| C _{oss} | - | 176 | - | | |
| C _{rss} | - | 141 | - | | |



Characteristics (Tc=25°C, unless otherwise specified)

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|---------------------------|------|------|------|------|--------------------------------------|
| Qg (VGS=10V) *1, 2 | - | 26 | - | nC | VDS=15V, VGS=10V, ID=16A |
| Qg (VGS=4.5V) *1, 2 | - | 19 | - | | |
| Qgs *1, 2 | - | 6.2 | - | | |
| Qgd *1, 2 | - | 10 | - | | |
| td(ON) *1, 2 | - | 7.5 | - | ns | VDS=15V, ID=1A, VGS=10V, RGS=2.7Ω |
| tr *1, 2 | - | 6.3 | - | | |
| td(OFF) *1, 2 | - | 30 | - | | |
| tf *1, 2 | - | 5 | - | | |
| Rg | - | 1.7 | - | Ω | VGS=15mV, VDS=0V, f=1MHz |
| Source-Drain Diode | | | | | |
| IS *1 | - | - | 5 | A | |
| ISM *3 | - | - | 20 | | |
| VSD *1 | - | - | 1.3 | V | IF=IS, VGS=0V |
| trr | - | 22 | - | ns | IF=IS, dIF/dt=100A/μs |
| Qrr | - | 12 | - | nC | |

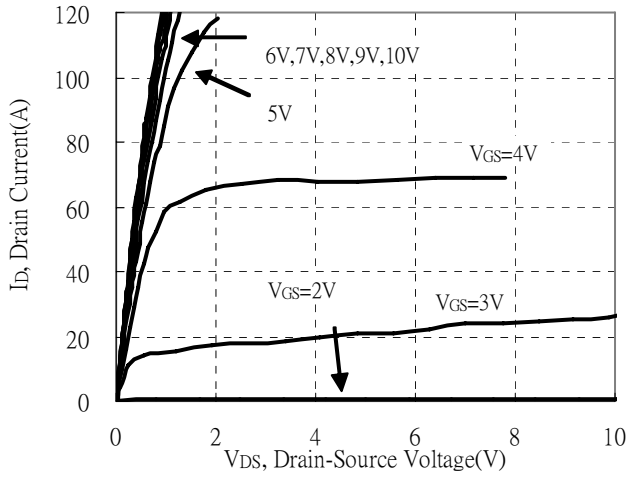
Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
 *2.Independent of operating temperature
 *3.Pulse width limited by maximum junction temperature.

Ordering Information

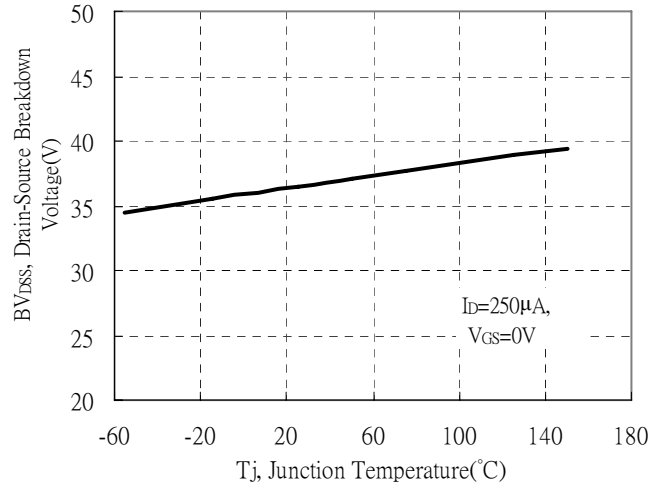
| Device | Package | Shipping | Marking |
|------------|---|------------------------|---------|
| MTB11N03Q8 | SOP-8 (Pb-free & Halogen-free package) | 2500 pcs / Tape & Reel | B11N03 |

Typical Characteristics

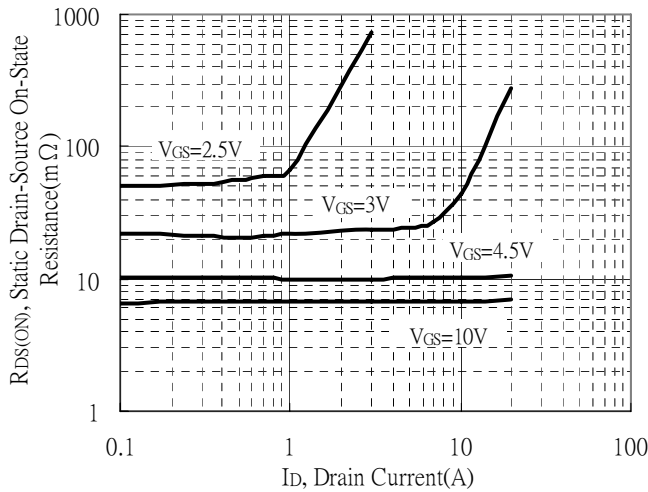
Typical Output Characteristics



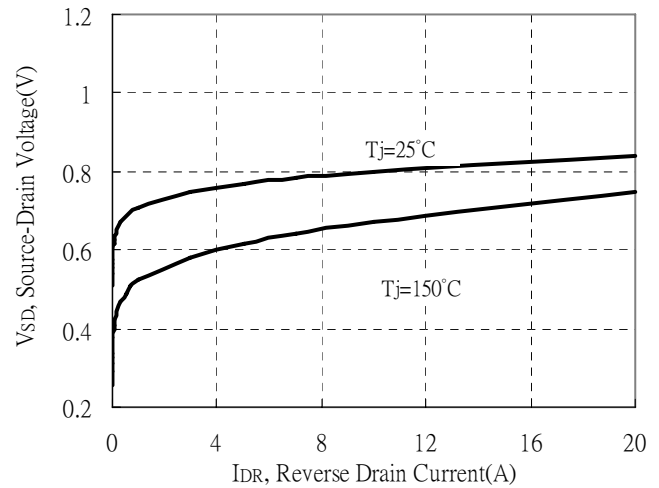
Brekdown Voltage vs Ambient Temperature



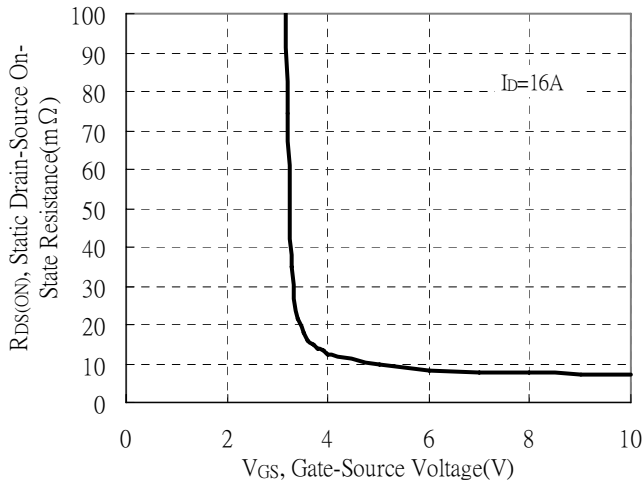
Static Drain-Source On-State resistance vs Drain Current



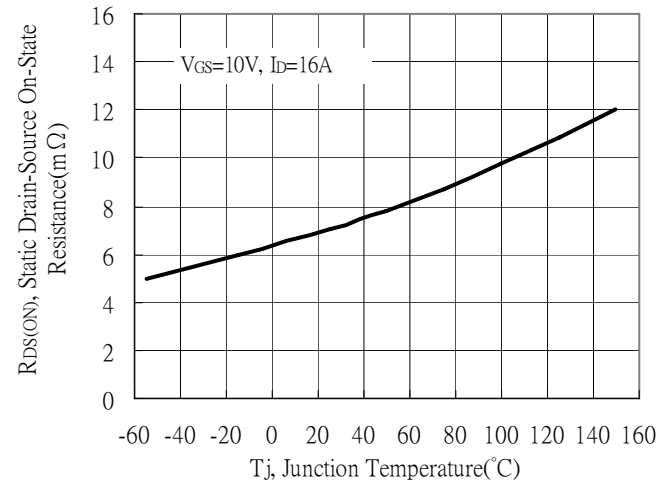
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

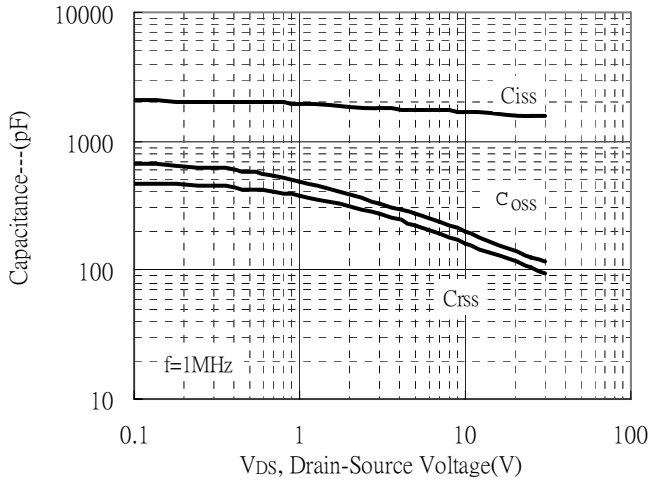


Drain-Source On-State Resistance vs Junction Temperature

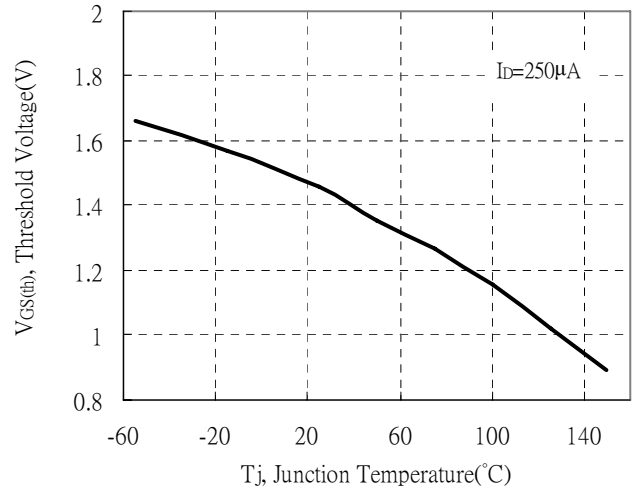


Typical Characteristics(Cont.)

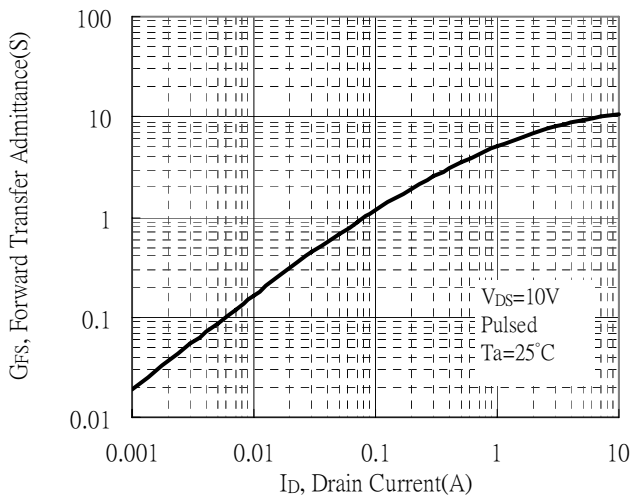
Capacitance vs Drain-to-Source Voltage



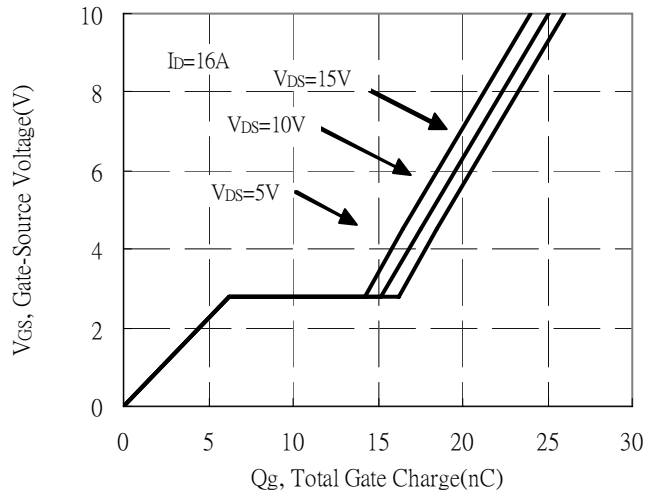
Threshold Voltage vs Junction Temperature



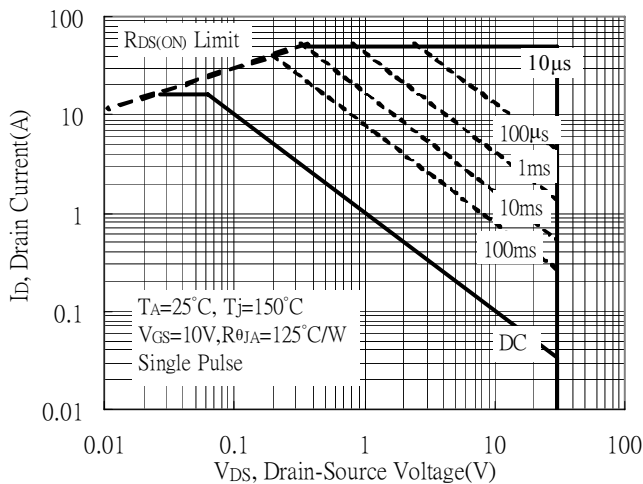
Forward Transfer Admittance vs Drain Current



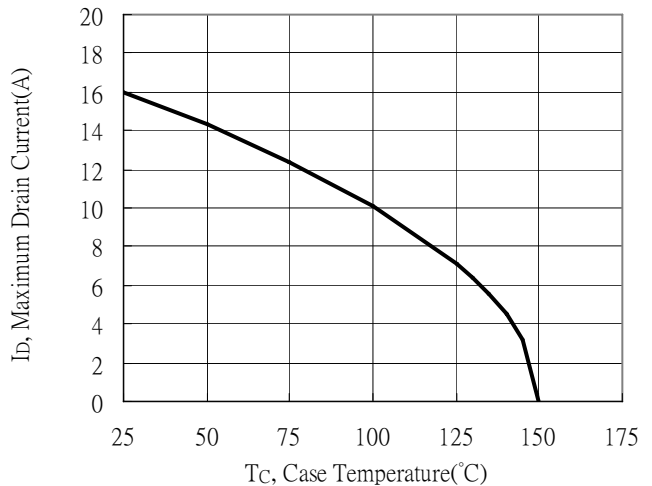
Gate Charge Characteristics



Maximum Safe Operating Area

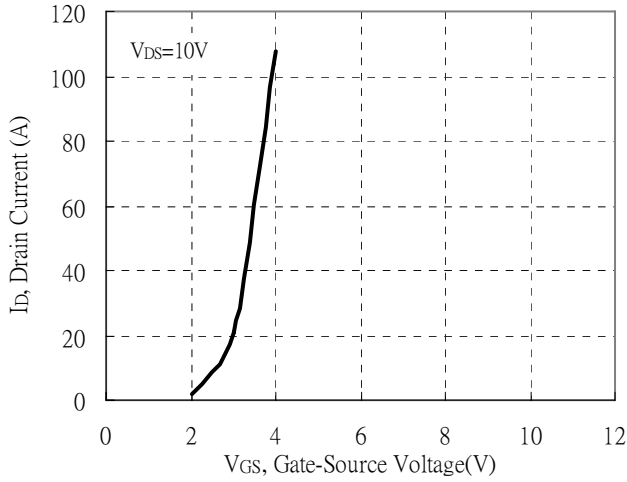


Maximum Drain Current vs Case Temperature

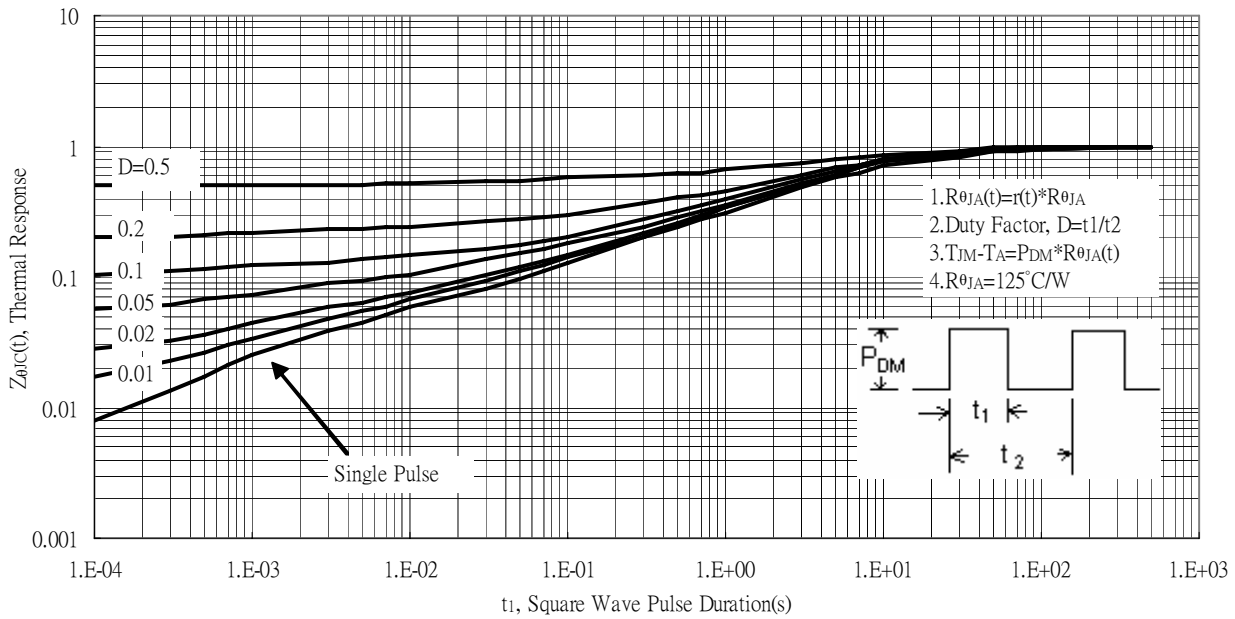


Typical Characteristics(Cont.)

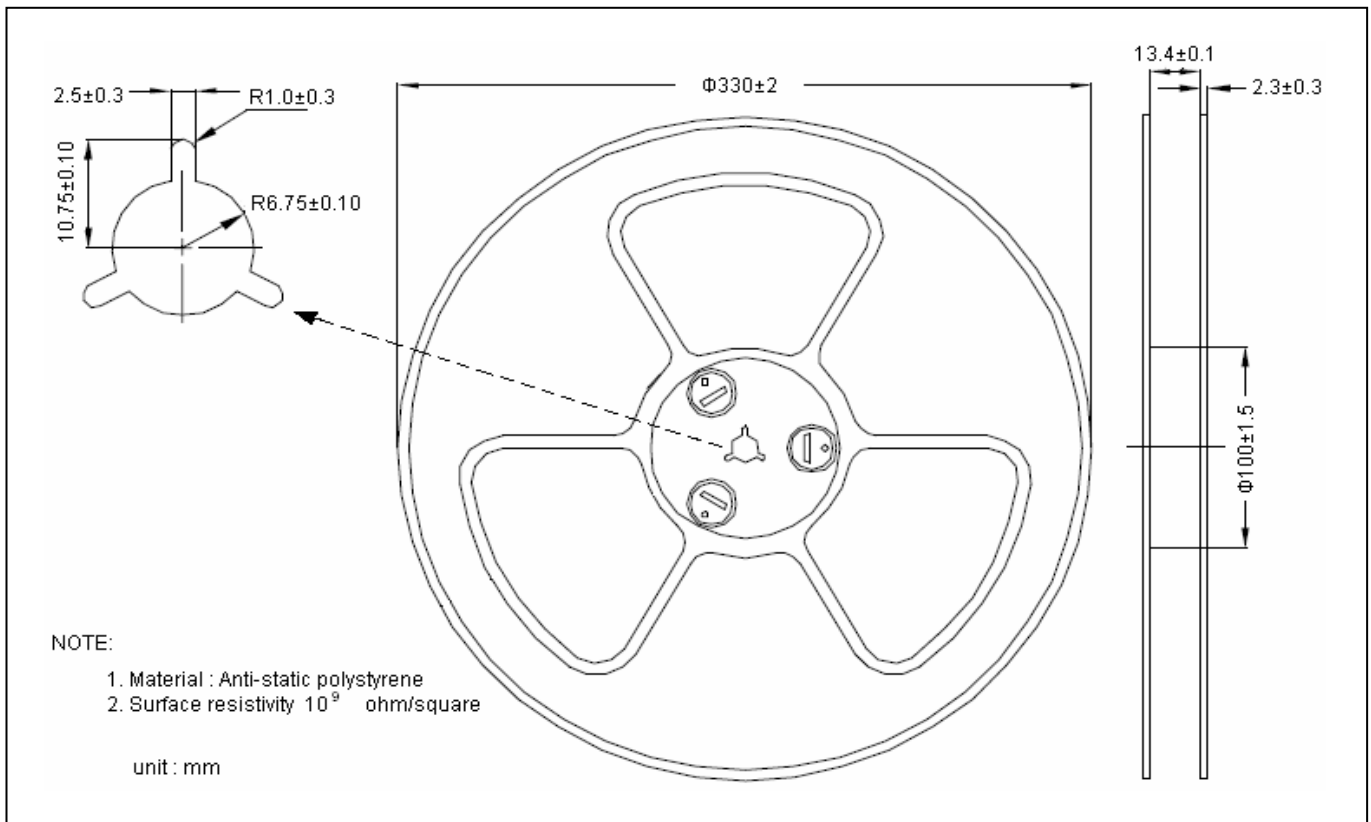
Typical Transfer Characteristics



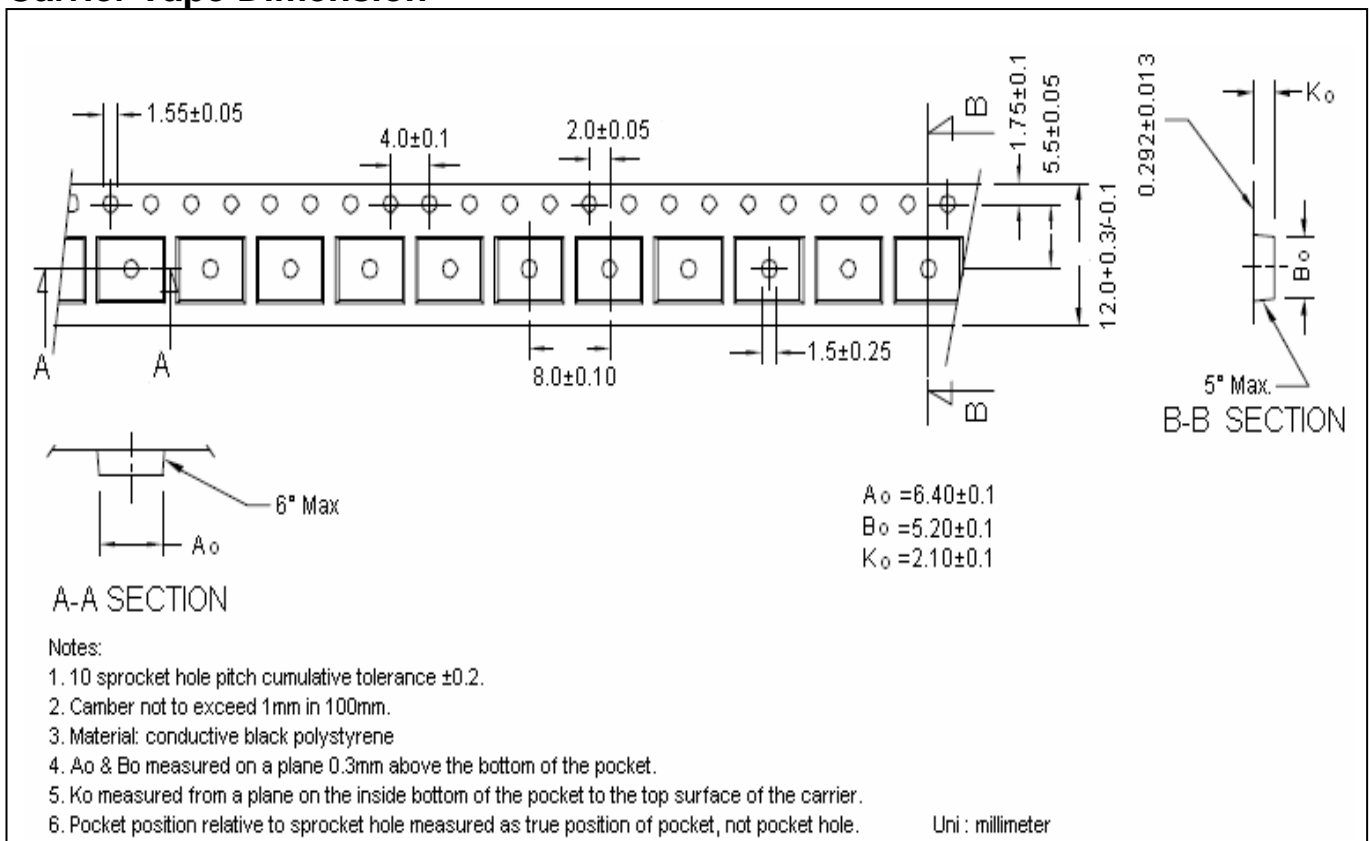
Transient Thermal Response Curves



Reel Dimension



Carrier Tape Dimension

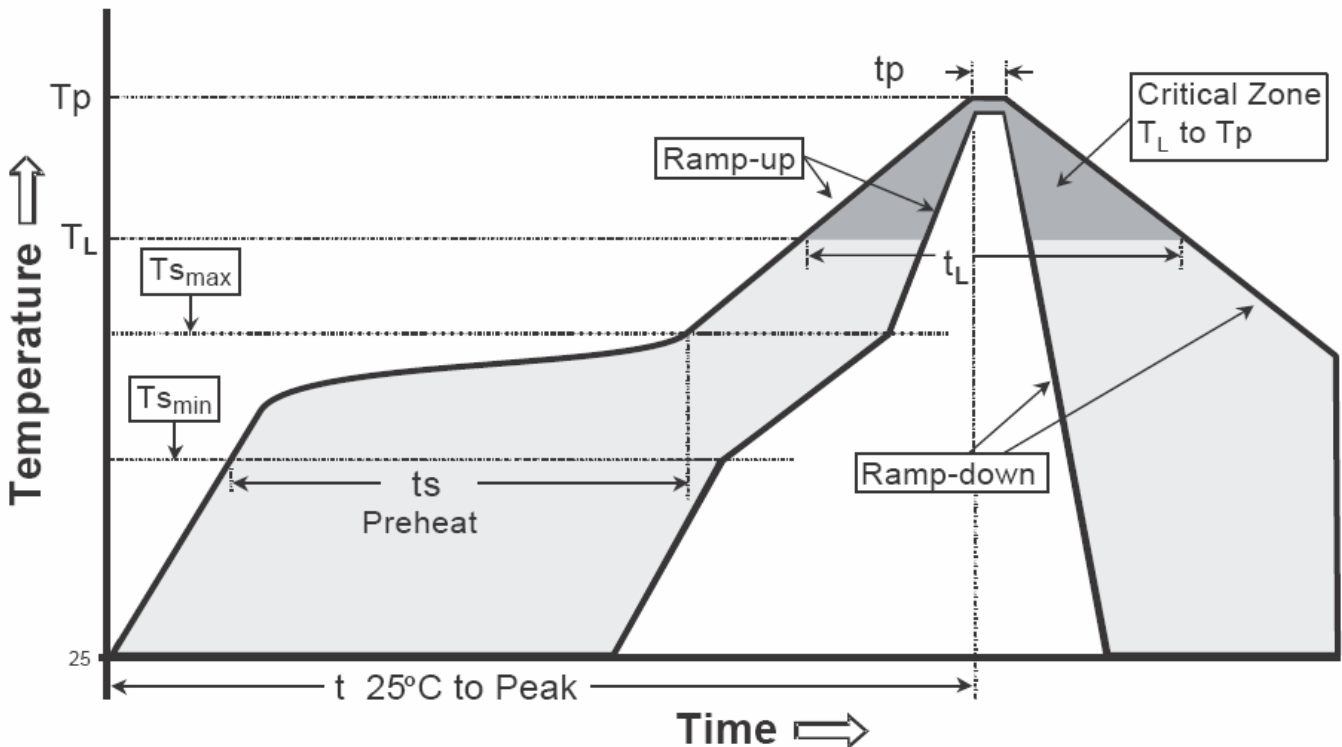




Recommended wave soldering condition

| | | |
|-----------------|------------------|-----------------|
| Product | Peak Temperature | Soldering Time |
| Pb-free devices | 260 +0/-5 °C | 5 +1/-1 seconds |

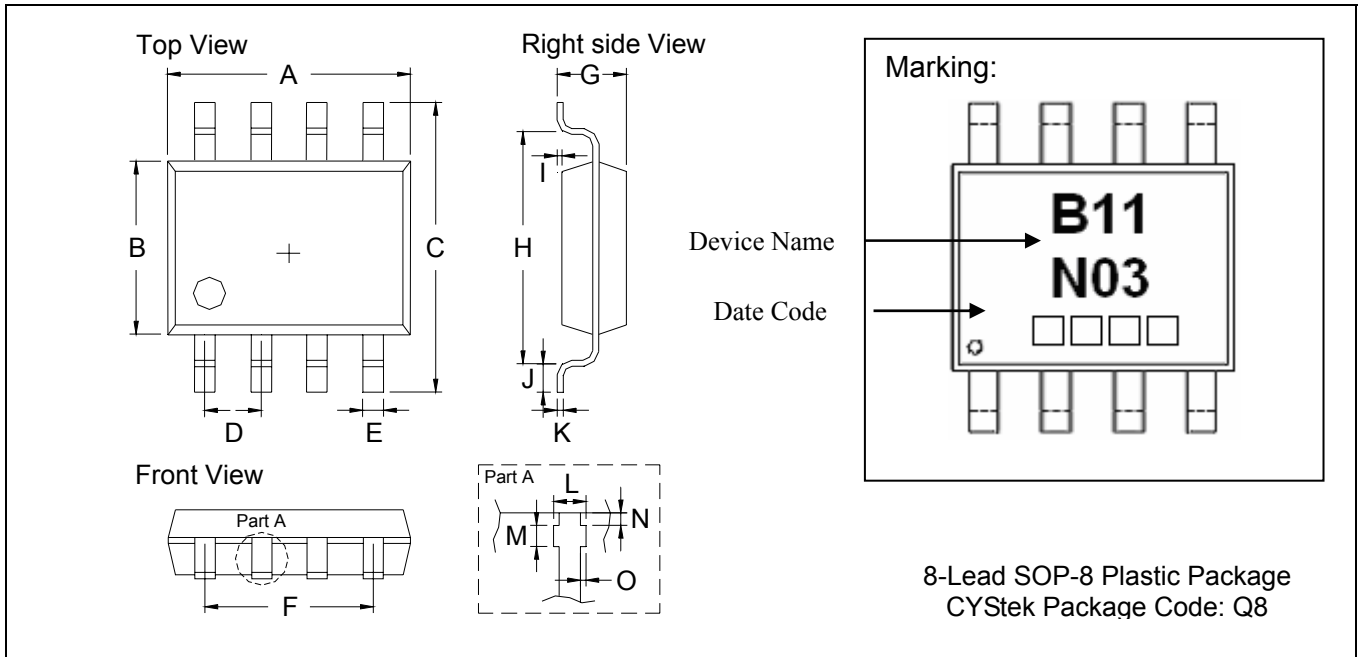
Recommended temperature profile for IR reflow



| Profile feature | Sn-Pb eutectic Assembly | Pb-free Assembly |
|--|-------------------------|------------------|
| Average ramp-up rate (Tsmax to Tp) | 3°C/second max. | 3°C/second max. |
| Preheat | | |
| -Temperature Min(Ts min) | 100°C | 150°C |
| -Temperature Max(Ts max) | 150°C | 200°C |
| -Time(ts min to ts max) | 60-120 seconds | 60-180 seconds |
| Time maintained above: | | |
| -Temperature (T _L) | 183°C | 217°C |
| - Time (t _L) | 60-150 seconds | 60-150 seconds |
| Peak Temperature(T _P) | 240 +0/-5 °C | 260 +0/-5 °C |
| Time within 5°C of actual peak temperature(tp) | 10-30 seconds | 20-40 seconds |
| Ramp down rate | 6°C/second max. | 6°C/second max. |
| Time 25 °C to peak temperature | 6 minutes max. | 8 minutes max. |

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOP-8 Dimension



*: Typical

| DIM | Inches | | Millimeters | | DIM | Inches | | Millimeters | |
|-----|--------|--------|-------------|------|-----|--------|--------|-------------|------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| A | 0.1909 | 0.2007 | 4.85 | 5.10 | I | 0.0019 | 0.0078 | 0.05 | 0.20 |
| B | 0.1515 | 0.1555 | 3.85 | 3.95 | J | 0.0118 | 0.0275 | 0.30 | 0.70 |
| C | 0.2283 | 0.2441 | 5.80 | 6.20 | K | 0.0074 | 0.0098 | 0.19 | 0.25 |
| D | 0.0480 | 0.0519 | 1.22 | 1.32 | L | 0.0145 | 0.0204 | 0.37 | 0.52 |
| E | 0.0145 | 0.0185 | 0.37 | 0.47 | M | 0.0118 | 0.0197 | 0.30 | 0.50 |
| F | 0.1472 | 0.1527 | 3.74 | 3.88 | N | 0.0031 | 0.0051 | 0.08 | 0.13 |
| G | 0.0570 | 0.0649 | 1.45 | 1.65 | O | 0.0000 | 0.0059 | 0.00 | 0.15 |
| H | 0.1889 | 0.2007 | 4.80 | 5.10 | | | | | |

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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